

L Number	Hits	Search Text	DB	Time stamp
1	20747	((crystal or crystalline or crystallographic) adj orientation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:29
2	89	(first adj (crystal or crystalline or crystallographic) adj orientation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:29
3	36	layer near10 (first adj (crystal or crystalline or crystallographic) adj orientation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:30
4	27	(layer near10 (first adj (crystal or crystalline or crystallographic) adj orientation))same (layer near10 (second adj (crystal or crystalline or crystallographic) adj orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:31
5	27	(layer near10 (first adj (crystal or crystalline or crystallographic) adj orientation)) same (layer near10 (second adj (crystal or crystalline or crystallographic) adj orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:39
6	0	(layer near10 (first adj (crystal or crystalline or crystallographic) adj orientation)) same (layer near10 (second adj (crystal or crystalline or crystallographic) adj orientation)) and (hybrid adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:34
7	0	((first adj (crystal or crystalline or crystallographic) adj orientation)) same ((second adj (crystal or crystalline or crystallographic) adj orientation)) and (hybrid adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:35
8	798	hybrid adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:36
9	26	(hybrid adj substrate) and ((crystal or crystalline or crystallographic) adj orientation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:37

12	0	((semiconductor adj layer) near3 (first adj (crystal or crystalline or crystallographic) adj orientation)) same ((semiconductor adj layer) near10 (second adj (crystal or crystalline or crystallographic) adj orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:40
11	3	((semiconductor adj layer) near3 (first adj (crystal or crystalline or crystallographic) adj orientation)) same (layer near10 (second adj (crystal or crystalline or crystallographic) adj orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:44
10	3	(semiconductor adj layer near3 (first adj (crystal or crystalline or crystallographic) adj orientation)) same (layer near10 (second adj (crystal or crystalline or crystallographic) adj orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:40
13	0	((semiconductor adj layer) near5 (first adj (crystal or crystalline or crystallographic) adj orientation)) same ((semiconductor adj layer) near5 (second adj (crystal or crystalline or crystallographic) adj orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:44
14	0	((semiconductor adj layer) near10 (first adj (crystal or crystalline or crystallographic) adj orientation)) same ((semiconductor adj layer) near10 (second adj (crystal or crystalline or crystallographic) adj orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:45
15	1	((semiconductor adj layer) near10 (first adj (crystal or crystalline or crystallographic) adj orientation)) and ((semiconductor adj layer) near10 (second adj (crystal or crystalline or crystallographic) adj orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:45
16	5	(ieong or reznicek or yang) and (hybrid adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:46
17	30	(ieong or reznicek or yang) and ((crystal or crystalline or crystallographic) adj orientation).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:47
18	8	(ieong or reznicek or yang) and (layer near10 ((crystal or crystalline or crystallographic) adj orientation)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:48

19	1	(ieong or reznicek or yang) and (layer near10 ((first or second) adj (crystal or crystalline or crystallographic) adj orientation)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:48
20	18	(layer near10 ((first or second) adj (crystal or crystalline or crystallographic) adj orientation)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:48
21	18	(layer near5 ((first or second) adj (crystal or crystalline or crystallographic) adj orientation)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:49
22	1	(semiconductor near5 layer near5 ((first or second) adj (crystal or crystalline or crystallographic) adj orientation)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:50
23	5	(semiconductor near5 layer near5 ((first or second) adj (crystal or crystalline or crystallographic) adj orientation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 20:50